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A Topmetal-based and High-Performance Resistance Measurement Circuit for the Thin-Film Sensitive Gas Detection

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We present the design and characterization of a high performance resistance measurement circuit fabricated in a standard $0.35\mu\text{m}$ CMOS process. The circuit implements two exposed metal electrodes in the topmost metal layer which can be deposited the sensitive thin-film. Test pulse is injected into one electrode, the other electrode is directly fed into a low noise charge sensitive amplifier with selective feedback capacitor. Simulations and initial tests show that the circuit achieved a $100\Omega \sim 100\text{T}\Omega$ measuring range and a 10Ω resolution. These characteristics enable its use as the accurate resistance monitoring sensor device in future thin-film sensitive gas detection applications.

Summary

We have successfully implemented a CMOS Integrated Circuit in a standard $0.35\mu\text{m}$ CMOS technology for high precision resistance measurement that is uniquely suitable in future gas concentration monitoring through the sensitive thin-film deposition. Based on the prototype of a series Topmetal pixel sensor with directly charge collection and excellent low noise performance, the front-end of this resistance measurement circuit implements two exposed metal electrodes which can be deposited the sensitive thin-film. The first electrode that measures $200\mu\text{m} \times 580\mu\text{m}$ area is named Topmetal. Around the Topmetal there is the second electrode named "Guard Ring, (Gring)" with $430\mu\text{m} \times 810\mu\text{m}$ area, which is a ring electrode in the same topmost metal layer as the Topmetal but isolated from it with $42\mu\text{m}$ distance. Test pulse generated by the internal or external Digital to Analog Converter (DAC) is injected into Gring, the Topmetal is directly fed into a low noise Charge Sensitive Amplifier (CSA) to generate analog voltage signal. The CSA is a dual-input folded cascode operational amplifier with $1\text{fF} \sim 50\text{pF}$ selective feedback capacitor (C_f). For expanding dynamic range and reducing noise, all biases of the CSA could be tunable through DACs with low-pass filters, respectively. The analog signal is routed through two stage source follower and an analogue output buffer to be accessed externally. The analog signal is also sampled by a high-resolution single-bit sigma-delta Analog to Digital Converter (ADC), which has a sampling rate of 25.6MHz for 200kHz input signal bandwidth and 80dB Signal to Noise Ratio (SNR). For a resistor (R_s) to be tested, we apply a calibrated square pulse with an amplitude of V_{TP} and a duration time of Δt to the Gring, the injected charge (Q_{in}) from Topmetal to CSA is defined by $Q_{in} = V_{TP}/R_s \cdot \Delta t$. The amplitude (VOM) response of the CSA is $VOM = (V_{TP} \cdot \Delta t)/(R_s \cdot C_f)$, thus the tested resistor could be derived by $R_s = (V_{TP} \cdot \Delta t)/(VOM \cdot C_f)$. According to our previous IC development Topmetal-II-, its C_f , maximal Q_{in} and Equivalent Noise Charge (ENC) are 5fF , $60000e^-$ and $13.9e^-$, respectively. Calculating by 10 times SNR, the effective measuring range of R_s reaches up to $100\Omega \sim 100\text{T}\Omega$. Simulations and initial tests show that the VOM of CSA is changed around 10mV with a 10Ω variation of R_s , which determines the minimum measuring resolution. These characteristics enable this circuit use as the accurate resistance monitoring sensor device in future thin-film sensitive gas detection applications. Further tests regarding the thin-film coating on the electrodes and gas concentration monitoring are ongoing. We will present the overall design and detailed test results of this circuit in the conference.

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